

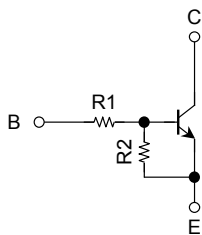
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process) (Bias Resistor Built-in Transistor)

RN1901FS,RN1902FS,RN1903FS RN1904FS,RN1905FS,RN1906FS

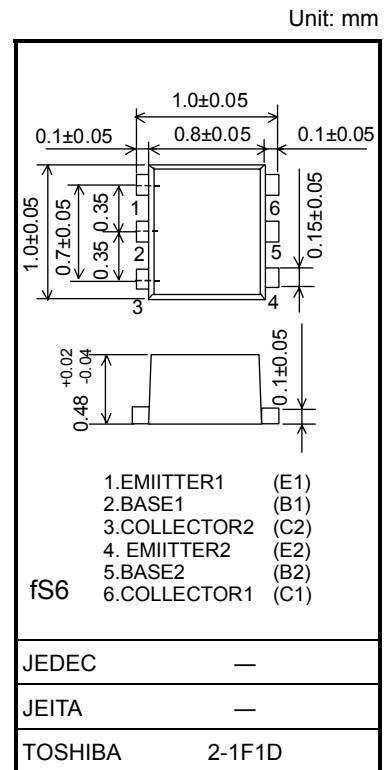
Switching, Inverter Circuit, Interface Circuit and
Driver Circuit Applications

- Two devices are incorporated into a fine pitch small mold (6-pin) package.
- Incorporating a bias resistor into a transistor reduces parts count. Reducing the parts count enables the manufacture of ever more compact equipment and lowers assembly cost.
- Complementary to RN2901FS~RN2906FS

Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN1901FS	4.7	4.7
RN1902FS	10	10
RN1903FS	22	22
RN1904FS	47	47
RN1905FS	2.2	47
RN1906FS	4.7	47



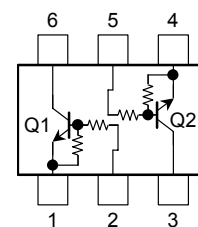
Weight: 0.001g (typ.)

Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	RN1901FS~1906FS V_{CBO}	20	V
Collector-emitter voltage	V_{CEO}	20	V
Emitter-base voltage	RN1901FS~1904FS V_{EBO}	10	V
	RN1905FS, 1906FS	5	V
Collector current	I_C	50	mA
Collector power dissipation	RN1901FS~1906FS P_C (Note)	50	mW
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-55~150	°C

Note: Total rating

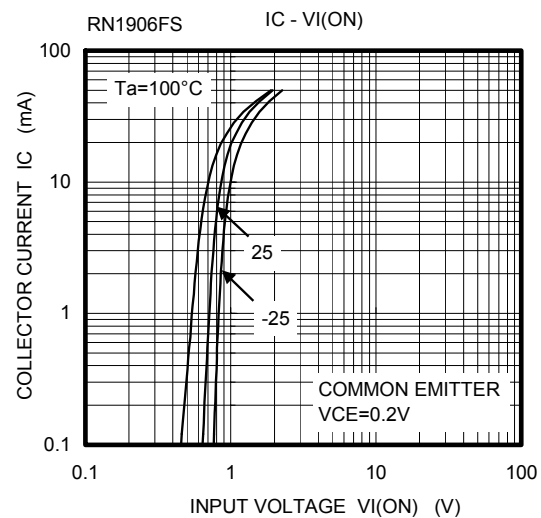
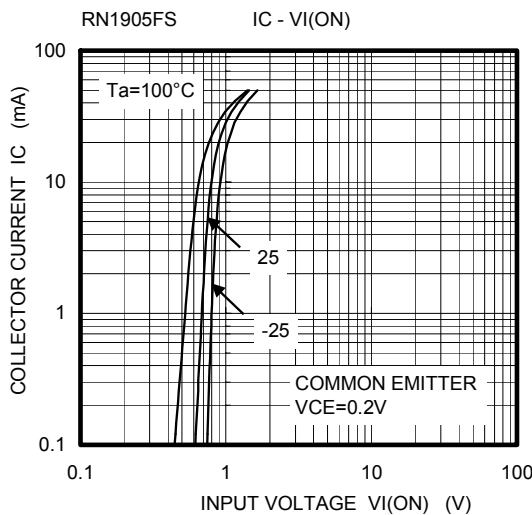
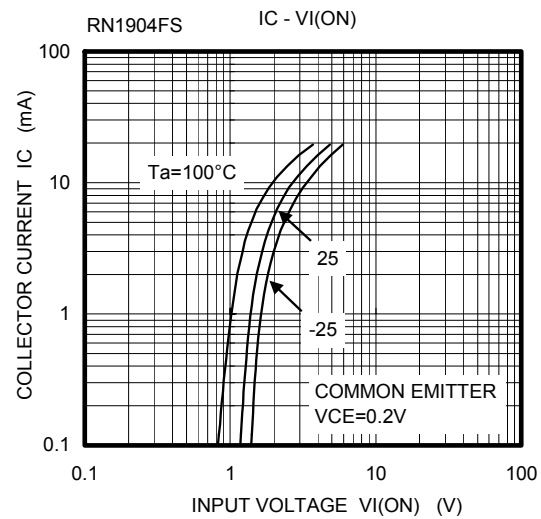
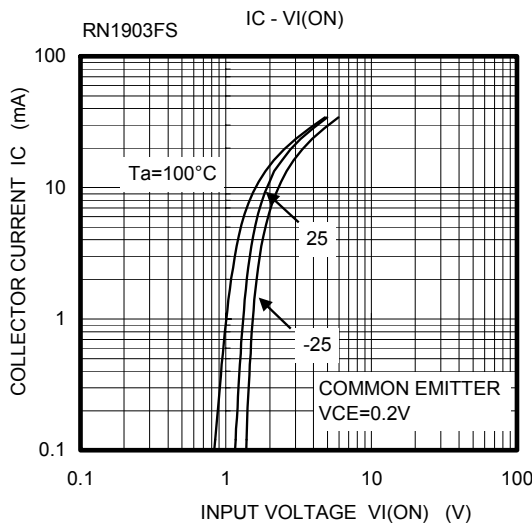
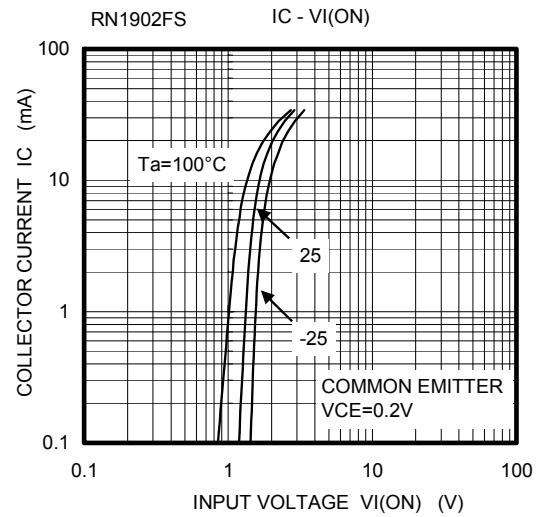
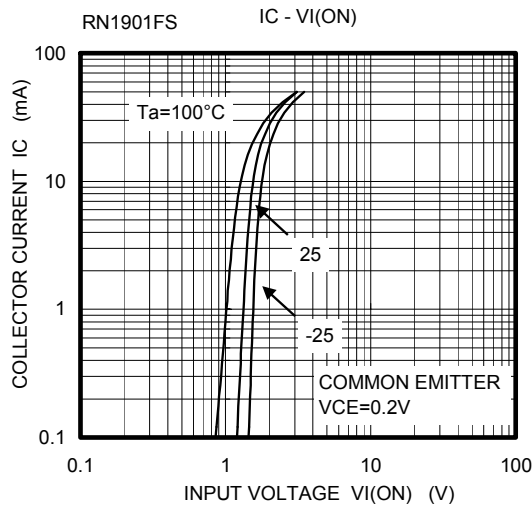
Equivalent Circuit (top view)



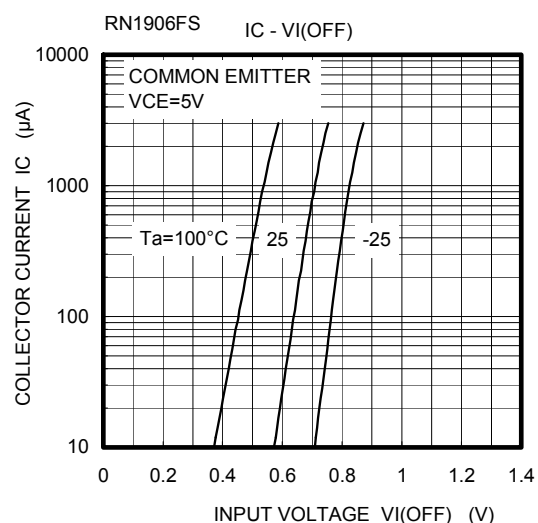
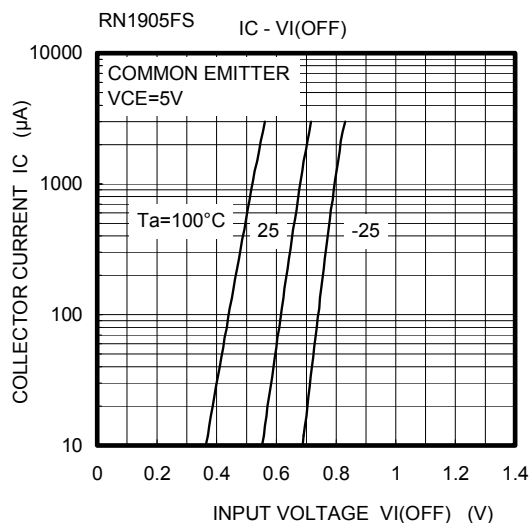
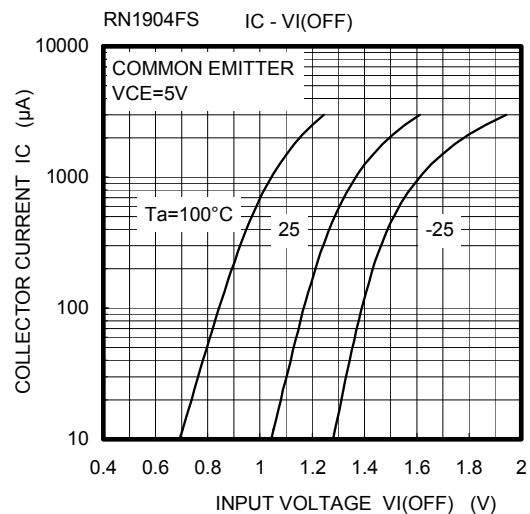
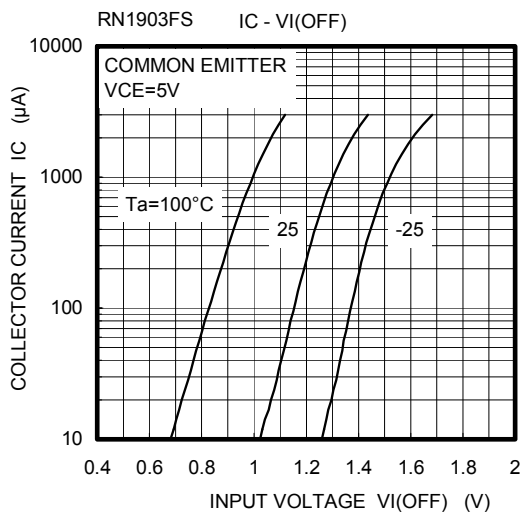
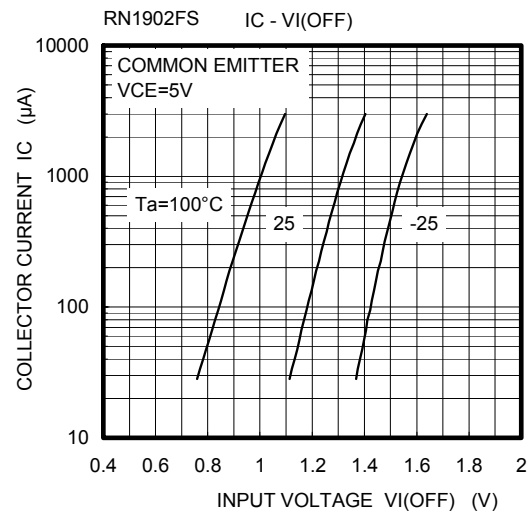
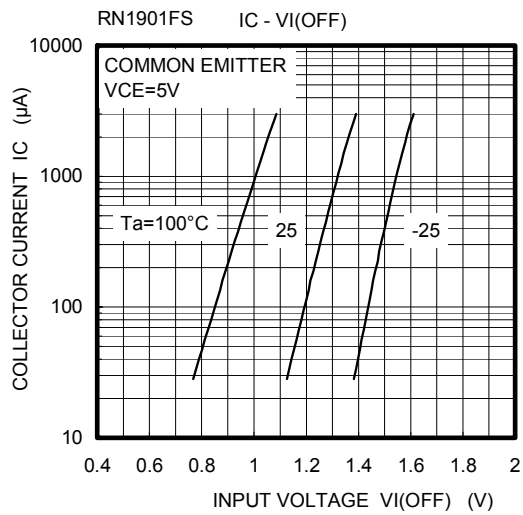
Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN1901FS~1906FS	I_{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$	—	—	100	nA
		I_{CEO}	$V_{CE} = 20 \text{ V}, I_B = 0$	—	—	500	
Emitter cut-off current	RN1901FS	I_{EBO}	$V_{EB} = 10 \text{ V}, I_C = 0$	0.89	—	1.33	mA
	RN1902FS			0.41	—	0.63	
	RN1903FS			0.18	—	0.29	
	RN1904FS			0.088	—	0.133	
	RN1905FS	I_{EBO}	$V_{EB} = 5 \text{ V}, I_C = 0$	0.085	—	0.127	
	RN1906FS			0.08	—	0.121	
DC current gain	RN1901FS	h_{FE}	$V_{CE} = 5 \text{ V}, I_C = 10 \text{ mA}$	30	—	—	
	RN1902FS			60	—	—	
	RN1903FS			100	—	—	
	RN1904FS			120	—	—	
	RN1905FS			120	—	—	
	RN1906FS			120	—	—	
Collector-emitter saturation voltage	RN1901FS~1906FS	$V_{CE(sat)}$	$I_C = 5 \text{ mA}, I_B = 0.25 \text{ mA}$	—	—	0.15	V
Input voltage (ON)	RN1901FS	$V_{I(ON)}$	$V_{CE} = 0.2 \text{ V}, I_C = 5 \text{ mA}$	1.0	—	2.0	V
	RN1902FS			1.0	—	2.2	
	RN1903FS			1.1	—	2.7	
	RN1904FS			1.2	—	3.6	
	RN1905FS			0.6	—	1.1	
	RN1906FS			0.6	—	1.2	
Input voltage (OFF)	RN1901FS~1904FS	$V_{I(OFF)}$	$V_{CE} = 5 \text{ V}, I_C = 0.1 \text{ mA}$	0.8	—	1.5	V
	RN1905FS, 1906FS			0.4	—	0.8	
Collector output capacitance	RN1901FS~1906FS	C_{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	—	1.2	—	pF
Input resistor	RN1901FS	R1	—	3.76	4.7	5.64	kΩ
	RN1902FS			8	10	12	
	RN1903FS			17.6	22	26.4	
	RN1904FS			37.6	47	56.4	
	RN1905FS			1.76	2.2	2.64	
	RN1906FS			3.76	4.7	5.64	
Resistor ratio	RN1901FS~1904FS	R1/R2	—	0.8	1.0	1.2	
	RN1905FS			0.0376	0.0468	0.0562	
	RN1906FS			0.08	0.1	0.12	

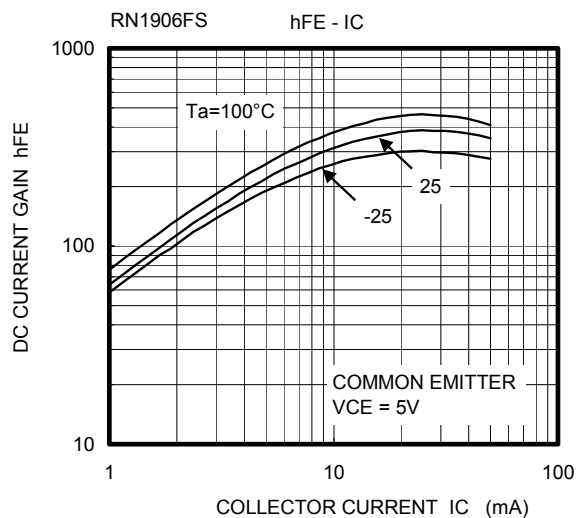
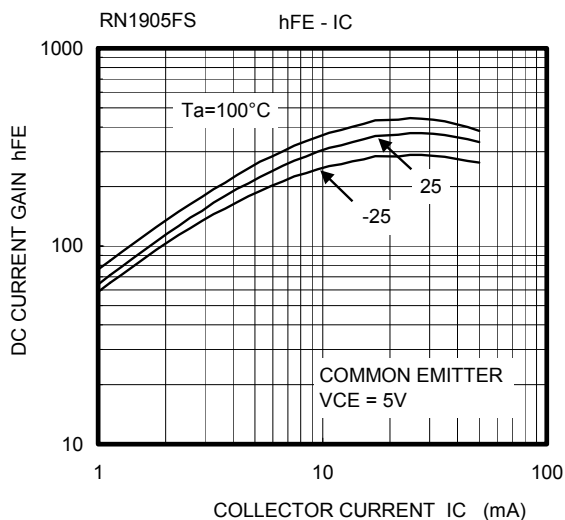
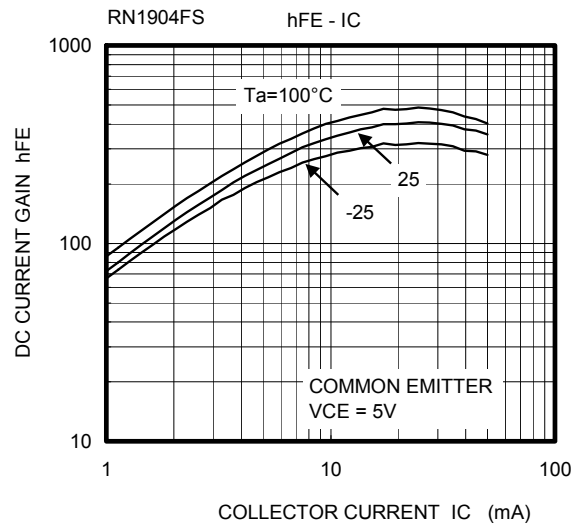
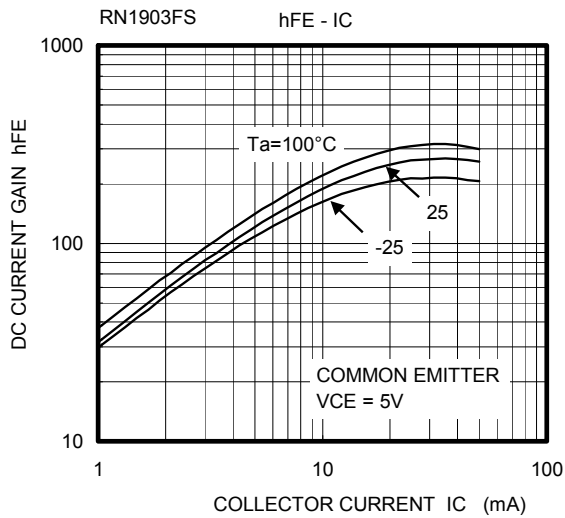
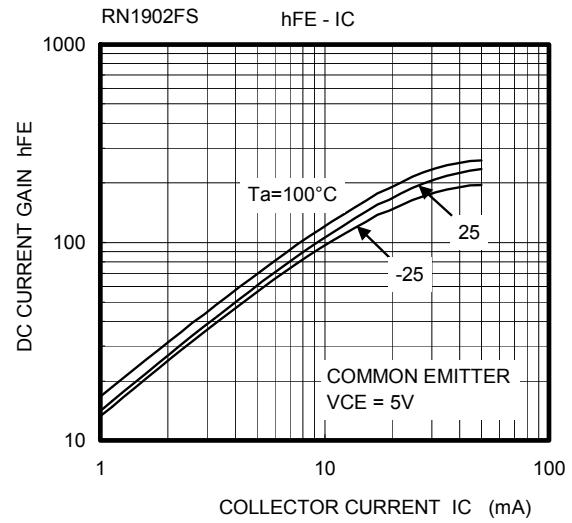
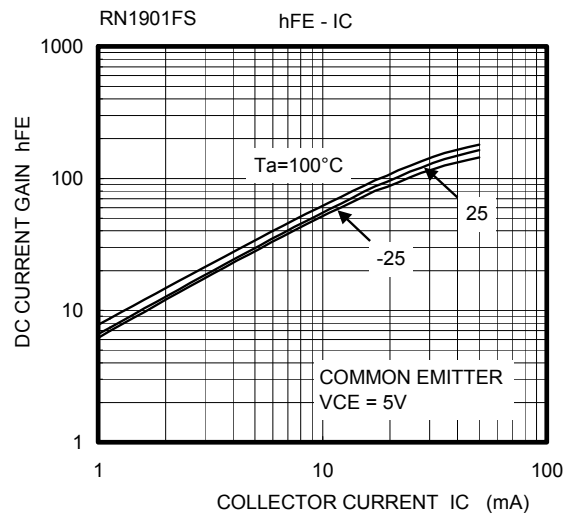
(Q1, Q2 Common)



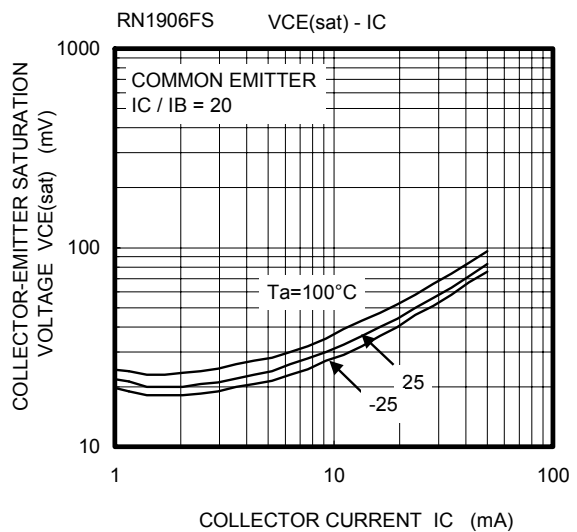
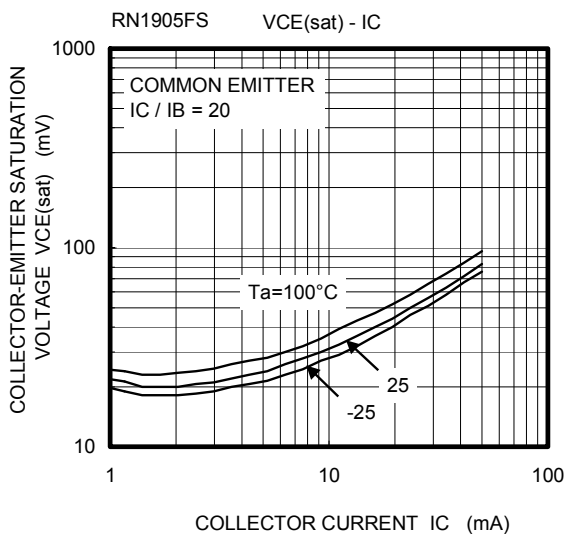
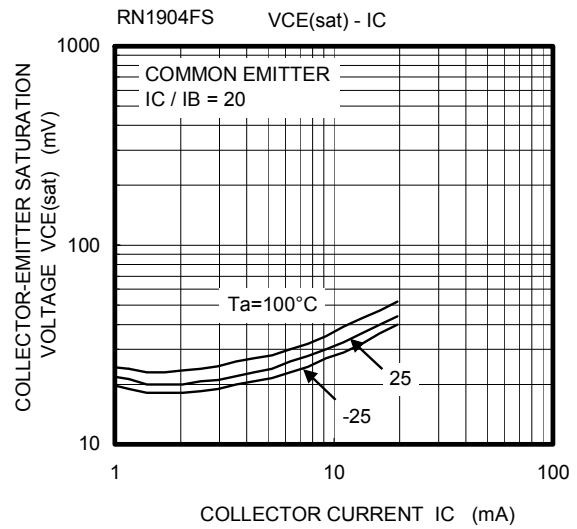
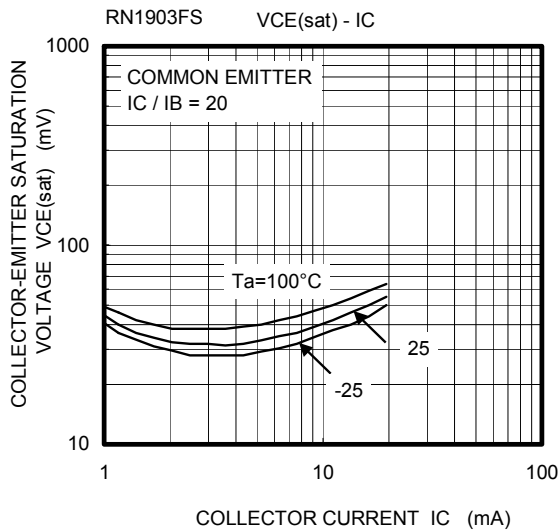
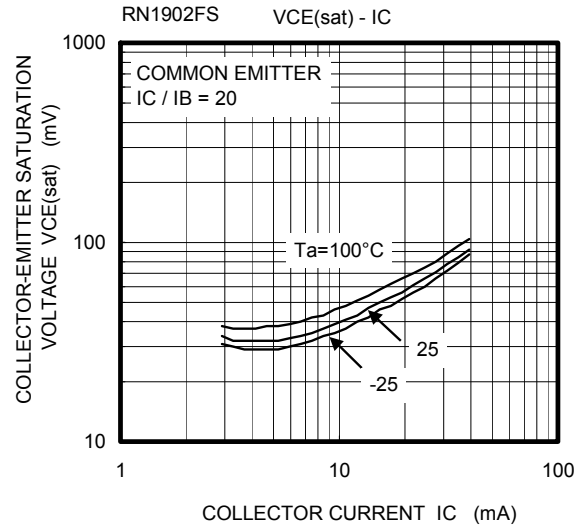
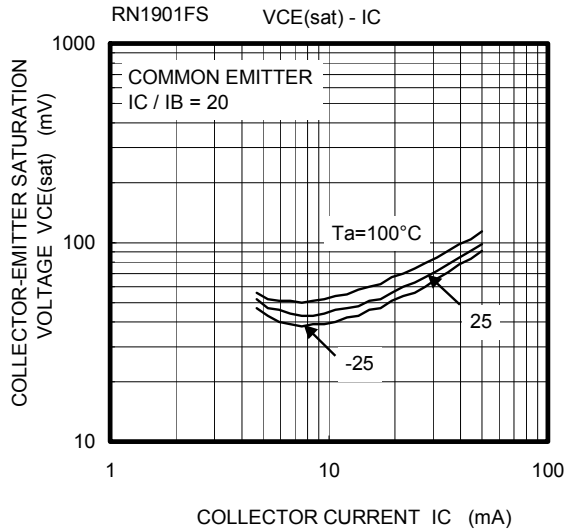
(Q1,Q2 Common)



(Q1,Q2 Common)



(Q1, Q2 Common)



Type Name	Marking
RN1901FS	
RN1902FS	
RN1903FS	
RN1904FS	
RN1905FS	
RN1906FS	

HANDLING PRECAUTION

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic discharge. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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